

Title (en)

PROCESS FOR THE PREPARATION OF POLYCRYSTALLINE SILICON LAYERS BY ELECTROLYTIC DEPOSITION OF SILICON

Publication

EP 0260223 B1 19910410 (DE)

Application

EP 87810460 A 19870813

Priority

CH 332086 A 19860819

Abstract (en)

[origin: US4759830A] A novel process for the electrolytic deposition of silicon from a melt containing covalent silicon compounds, in particular silicon tetrahalides, and furthermore aluminum halides, alkali metal halides and halides of transition metals is carried out at relatively low temperatures of 100 DEG to 350 DEG C. in an inert temperature. The silicon is deposited cathodically or anodically onto electrically conductive material. The silicon coatings are homogeneous and adhere firmly to the substrate. The coated materials can be used for the production of photoconductive or photovoltaic devices.

IPC 1-7

C25D 3/66

IPC 8 full level

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CPC (source: EP US)

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Cited by

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DOCDB simple family (publication)

EP 0260223 A1 19880316; **EP 0260223 B1 19910410**; AU 587713 B2 19890824; AU 7715587 A 19880225; DE 3769252 D1 19910516; ES 2021751 B3 19911116; IL 83570 A0 19880131; IL 83570 A 19910131; JP S6350496 A 19880303; US 4759830 A 19880726; US 4773973 A 19880927; ZA 876100 B 19880219

DOCDB simple family (application)

EP 87810460 A 19870813; AU 7715587 A 19870818; DE 3769252 T 19870813; ES 87810460 T 19870813; IL 8357087 A 19870817; JP 20429087 A 19870819; US 16549288 A 19880308; US 8763587 A 19870818; ZA 876100 A 19870818